

Abstract

A method for producing semiconductor integrated circuit devices and a semiconductor integrated circuit device produced by the method are provided. In the method, when a first select gate electrode (G2a, G2b) and a second select gate electrode (G3a, G3b) that are independently controllable are formed in a production process, an extra dedicated photomask process for electrically separating the first select gate electrode (G2a, G2b) and the second select gate electrode (G3a, G3b) is not needed in addition to a conventional dedicated photomask process of fabricating a memory circuit region only, thereby achieving reduction in a production cost accordingly.